

2SD2357

Silicon NPN epitaxial planer type

For low-frequency amplification

Complementary to 2SB1537

Features

- Low collector to emitter saturation voltage $V_{CE(sat)}$.
- Large collector power dissipation P_C .
- Mini Power type package, allowing downsizing of the equipment and automatic insertion through the tape packing and the magazine packing.

Absolute Maximum Ratings ($T_a=25^\circ\text{C}$)

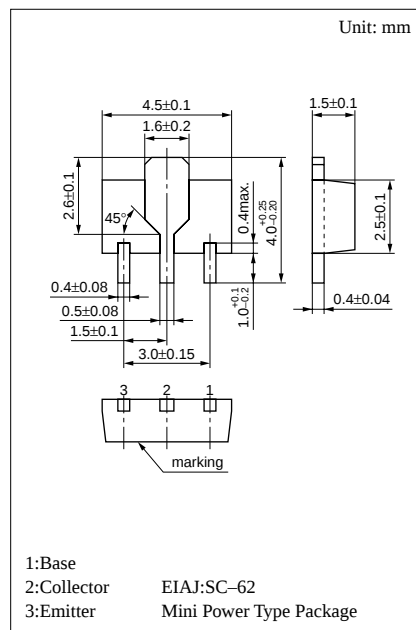
Parameter	Symbol	Ratings	Unit
Collector to base voltage	V_{CBO}	10	V
Collector to emitter voltage	V_{CEO}	10	V
Emitter to base voltage	V_{EBO}	5	V
Peak collector current	I_{CP}	1.2	A
Collector current	I_C	1	A
Collector power dissipation	P_C^*	1	W
Junction temperature	T_j	150	$^\circ\text{C}$
Storage temperature	T_{stg}	$-55 \sim +150$	$^\circ\text{C}$

* Printed circuit board: Copper foil area of 1cm^2 or more, and the board thickness of 1.7mm for the collector portion

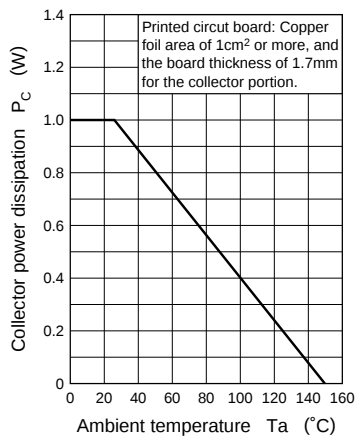
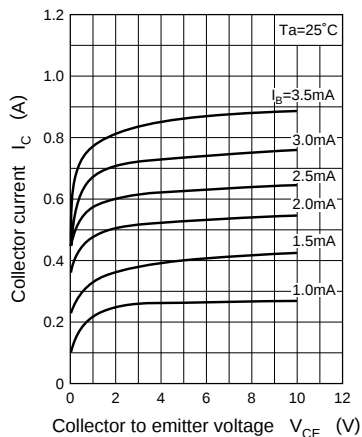
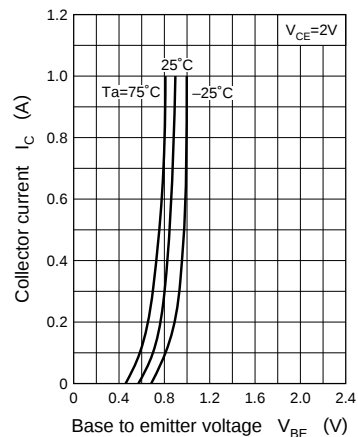
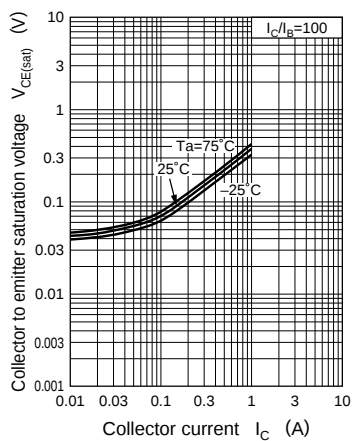
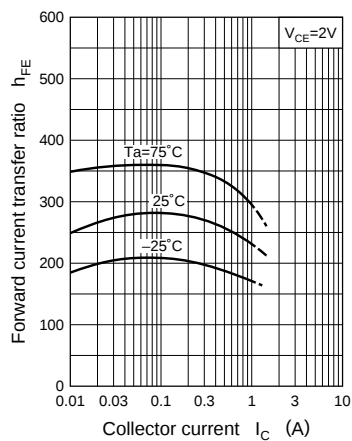
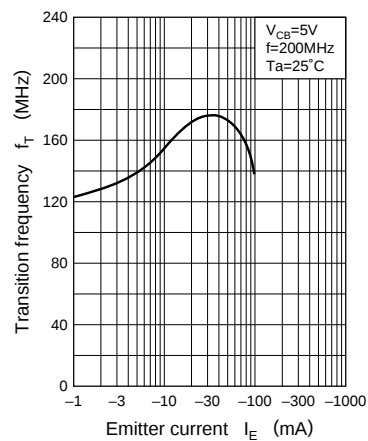
Electrical Characteristics ($T_a=25^\circ\text{C}$)

Parameter	Symbol	Conditions	min	typ	max	Unit
Collector cutoff current	I_{CBO}	$V_{CB} = 7\text{V}, I_E = 0$			1	μA
Collector to base voltage	V_{CBO}	$I_C = 10\mu\text{A}, I_E = 0$	10			V
Collector to emitter voltage	V_{CEO}	$I_C = 1\text{mA}, I_B = 0$	10			V
Emitter to base voltage	V_{EBO}	$I_E = 10\mu\text{A}, I_C = 0$	5			V
Forward current transfer ratio	h_{FE}	$V_{CE} = 2\text{V}, I_C = 100\text{mA}^{**}$	200		800	
Collector to emitter saturation voltage	$V_{CE(sat)}$	$I_C = 500\text{mA}, I_B = 5\text{mA}$			0.15	V
Transition frequency	f_T	$V_{CB} = 5\text{V}, I_E = -50\text{mA}, f = 200\text{MHz}$		120		MHz
Collector output capacitance	C_{ob}	$V_{CB} = 5\text{V}, I_E = 0, f = 1\text{MHz}$		30		pF

** Pulse measurement



Marking symbol : 1M

$P_C - T_a$  $I_C - V_{CE}$  $I_C - V_{BE}$  $V_{CE(sat)} - I_C$  $h_{FE} - I_C$  $f_T - I_E$  $C_{ob} - V_{CB}$ 